

# **TSM2302**

## 20V N-Channel MOSFET



SOT-23

#### Pin Definition:



- 1. Gate 2. Source
- 3. Drain

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
20	65 @ V <sub>GS</sub> = 4.5V	2.8	
	95 @ V <sub>GS</sub> = 2.5V	2.0	

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

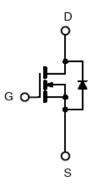
#### **Application**

- Load Switch
- PA Switch

### **Ordering Information**

Part No.	Package	Packing
TSM2302CX RF	SOT-23	3Kpcs / 7" Reel

#### **Block Diagram**



N-Channel MOSFET

### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		$V_{DS}$	20	V	
Gate-Source Voltage		$V_{GS}$	±8	V	
Continuous Drain Current, V <sub>GS</sub> @4.5V		I <sub>D</sub>	2.8	А	
Pulsed Drain Current, V <sub>GS</sub> @4.5V		I <sub>DM</sub>	8	Α	
Continuous Source Current (Diode Co	nduction) <sup>a,b</sup>	Is	1.6	А	
Maximum Power Dissipation	Ta = 25°C	D	1.25	W	
	Ta = 75°C	$ P_{D}$	0.8		
Operating Junction Temperature		$T_J$	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ <sub>JF</sub>	75	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO <sub>JA</sub>	145	°C/W

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#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.

Version: B07



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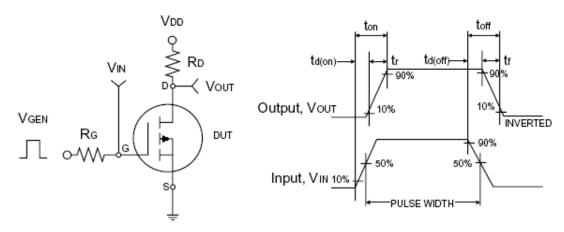


**Electrical Specifications** 

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	•	•		•		
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 250 \mu A$	BV <sub>DSS</sub>	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	0.65	0.95	1.2	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	μA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I <sub>D(ON)</sub>	6			Α
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 2.8A$	В		40	65	mΩ
Dialii-Source Oii-State Resistance	$V_{GS} = 2.5V, I_D = 2.0A$	$R_{DS(ON)}$		50	95	
Forward Transconductance	$V_{DS} = 5V, I_D = 2.8A$	g <sub>fs</sub>		10		S
Diode Forward Voltage	I <sub>S</sub> = 1.6A, V <sub>GS</sub> = 0V	$V_{SD}$		0.76	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	$V_{DS} = 10V, I_D = 2.8A,$	$Q_g$		5.4	10	
Gate-Source Charge	$V_{DS} = 10V, I_D = 2.6A,$ $V_{GS} = 4.5V$	$Q_gs$		0.65		nC
Gate-Drain Charge	V <sub>GS</sub> = 4.5V	$Q_{gd}$		1.4		
Input Capacitance	\/ - 40\/ \/ - 0\/	C <sub>iss</sub>		340		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		115		pF
Reverse Transfer Capacitance	1 - 1.0WITZ	$C_{rss}$		33		
Switching <sup>c</sup>						
Turn-On Delay Time	V - 0V D - 400	t <sub>d(on)</sub>		12	25	
Turn-On Rise Time	$V_{DD} = 6V, R_L = 10\Omega,$	t <sub>r</sub>		36	60	nS
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 4.5V,$ $R_G = 6\Omega$	t <sub>d(off)</sub>		34	60	110
Turn-Off Fall Time	1/C - 077	t <sub>f</sub>		10	25	

#### Notes:

- a. pulse test: PW □300μS, duty cycle □2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

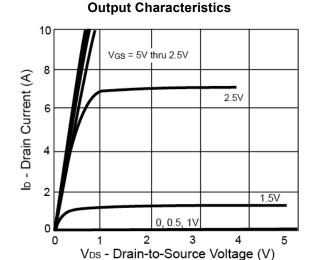




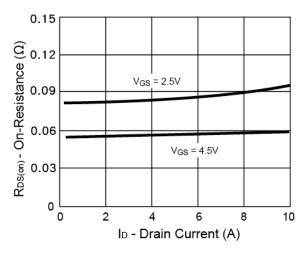
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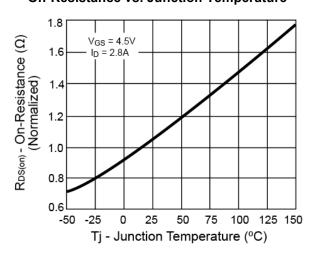
#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



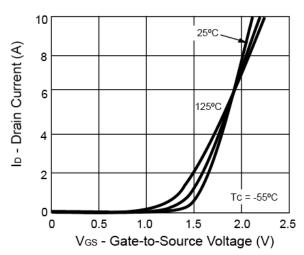
#### **On-Resistance vs. Drain Current**



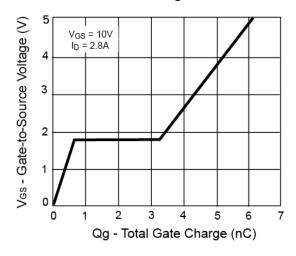
#### On-Resistance vs. Junction Temperature



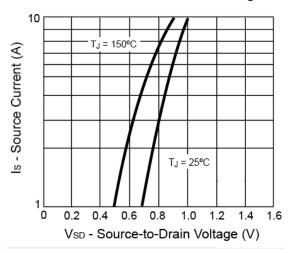
#### **Transfer Characteristics**



**Gate Charge** 



#### Source-Drain Diode Forward Voltage



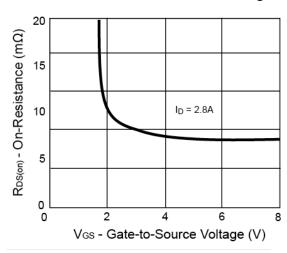


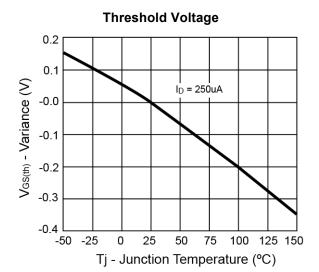




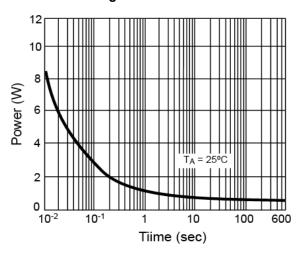
## **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

#### On-Resistance vs. Gate-Source Voltage

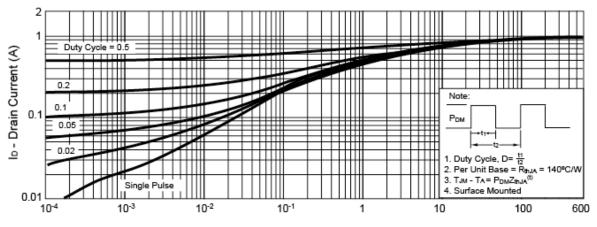




#### **Single Pulse Power**



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



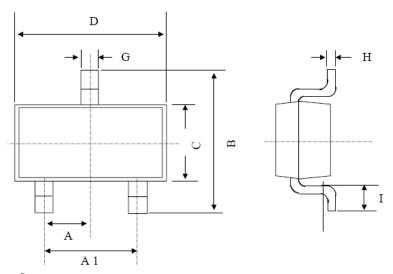
Square Wave Pulse Duration (sec)



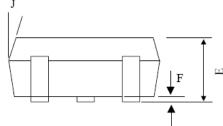




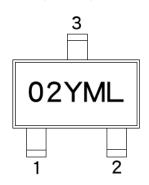
## **SOT-23 Mechanical Drawing**



SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.95	BSC	0.037 BSC		
A1	1.9 I	1.9 BSC		BSC	
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Е	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
I	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



## **Marking Diagram**



02 = Device Code

Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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